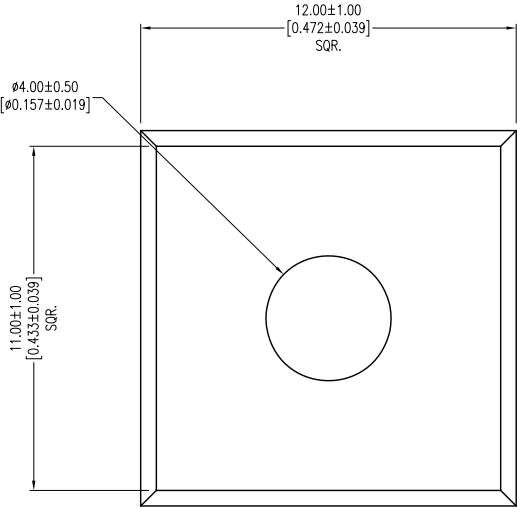




ELECTRO-OPTICAL CHARACTERISTICS:

PARAMETER	SYM	MIN	TYP	MAX	UNITS	TEST COND
FORWARD VOLTAGE	Vf1	1.35			V	If=10μA
	Vf2	1.9	2.0	2.2	V	If=20mA
REVERSE CURRENT	Ir			2	μA	Vr=-10V
PEAK WAVELENGTH	λp		592		nm	If=20mA
DOMINANT WAVELENGTH	λd	588	590	592	nm	If=20mA
SPECTRA HALF-WIDTH	Δλ		10		nm	If=20mA
LUMINOUS INTENSITY(1)	Iv	130	152	170	mcd	If=20mA

1. Iv (ave.) IS THE AVERAGE LUMINOUS INTENSITY OF OVERALL QUALIFIED CHIPS FROM INDIVIDUAL EPIWAFER.
2. TEMP (MAX) FOR CHIP PACKAGE CANNOT EXCEED 300°C.

CAUTION: STATIC SENSITIVE DEVICE
FOLLOW PROPER E.S.D. HANDLING PROCEDURES
WHEN WORKING WITH THIS PART.

